AMENDMENTS TO THE SPECIFICATION

Please replace paragraphs [0033] and [0034] with the following amended paragraphs:

[0033] FIG. 3C is a top elevation view depicting an exemplary embodiment of tapered signal lines 310. In this exemplary embodiment, spatial separation distances [[301,]] 302, 303, 304 and 305 between a shielding line 129 and a tapered signal line 310 get progressively larger on one side of tapered signal line 310, and spatial separation distance 306 stays at least substantially the same on an opposite side of tapered signal line 310. Again, stepped tapering on only one side of a line may be done on a shielding line or a signal line or a combination thereof provided parasitic capacitance progressively decreases from an input end to an output end.

[0034] FIG. 3D is a perspective view depicting a tapered signal line 310 of FIG. 3C. Notably, though width 351 is larger than width 352, sidewall height 102 is substantially the same. Furthermore, widths 351, 352, 353 and 344 [[354]] reflect a progression of inward stepwise indentations to tapered signal line 310 in increments, while sidewall height 102 is at least substantially the same throughout the extent of tapered signal line 310 [[401]]. FIG. 3D in one embodiment shows a tapered conductive wire or tapered metal trace with a substantially horizontal surface 354 and a substantially vertical surface 355. The vertical surface may, in this case, be referred to as a sidewall with height 102.

Please replace the Abstract paragraph with the following amended paragraph:

Method and apparatus for a forming aAn integrated circuit including a plurality of conductive wires is described. A first wire having sidewalls is tapered from the proximal end to the distal end to reduce width from the first width to the second width. A second wire, spaced apart from the first wire, the second wire has sidewalls. The first wire and the second wire are each horizontally disposed along side each other

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forming a part of a sidewall capacitor between facing sidewalls. The sidewall capacitor capacitance is progressively reduced responsive to the first wire taper.

PATENT

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